IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Chen *et al.*

Appl. No. 10/643,957

Filed: August 20, 2003

For: **High Voltage Power Management Unit Architecture in CMOS Process**

Confirmation No.: 4983

Art Unit: 2838

Examiner: Patel, Rajnikant B.

Atty. Docket: 1875.4170000/JTH/GSB

DECLARATION UNDER 37 C.F.R. § 1.131
By George S. Bardmesser

Commissioner for Patents
Washington, D.C. 20231

Sir:

The undersigned, George S. Bardmesser, declares and states that,

1. I am a patent attorney with the firm of Sterne, Kessler, Goldstein & Fox, P.L.L.C. I have been responsible for the drafting of the above-captioned application, U.S. Patent Application No. 10/643,957, filed on August 20, 2003.

2. Prior to July 20, 2003, I began working on preparation of the above-captioned application. A copy of the time entries for this matter, which had been assigned our internal docket number 1875.4170000 (and related matters 1875.4150000, now U.S. Patent Application No. 10/643,956 and 1875.4160000, now U.S. Patent Application No. 10/643,955, all of which have the same specification), is attached as Exhibit A to this Declaration. Exhibit A shows the work on the application beginning prior to July 20, 2003, and progressing steadily up through the filing date of the application (August 20, 2003), for myself and my colleague, Jeffrey T. Helvey.

3. Additionally, a copy of the cover letter forwarding a final draft to the inventors on August 11, 2003 is attached as Exhibit B.

4. That all statements made of my own knowledge are true and that all statements made on information and belief are believed to be true; and further acknowledges that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

By: _____ 2/18/05
George S. Bardmesser Date

Timekeeper	Date	Client	Matter	Matter Desc	Hours	Description
GS Bardmesser	04/25/2003	1875	4170000	High Voltage Power M	5.20	prepare and forward application to inventor for review (4/25 - 7/10/03: G. Bardmesser & J. Helvey);
GS Bardmesser	04/29/2003	1875	4170000	High Voltage Power M	2.60	work on application, specification, claims and figures;
GS Bardmesser	04/30/2003	1875	4170000	High Voltage Power M	2.00	work on application, specification, claims and figures;
GS Bardmesser	05/01/2003	1875	4170000	High Voltage Power M	1.80	work on application, specification, claims and figures;
GS Bardmesser	05/05/2003	1875	4170000	High Voltage Power M	1.80	work on application, specification, claims and figures;
GS Bardmesser	05/08/2003	1875	4170000	High Voltage Power M	(1.90)	Maintenance Change.
GS Bardmesser	05/08/2003	1875	4170000	High Voltage Power M	1.90	work on application, specification, claims and figures;
GS Bardmesser	05/09/2003	1875	4170000	High Voltage Power M	1.90	work on application, specification, claims and figures;
GS Bardmesser	05/13/2003	1875	4170000	High Voltage Power M	2.20	work on application, specification, claims and figures;
GS Bardmesser	05/14/2003	1875	4170000	High Voltage Power M	1.40	work on application, specification, claims and figures;
GS Bardmesser	05/15/2003	1875	4170000	High Voltage Power M	1.50	work on application, specification, claims and figures;
GS Bardmesser	05/16/2003	1875	4170000	High Voltage Power M	2.20	work on application, specification, claims and figures;
GS Bardmesser	05/19/2003	1875	4170000	High Voltage Power M	0.70	work on application, specification, claims and figures;
GS Bardmesser	05/20/2003	1875	4170000	High Voltage Power M	1.70	file non-provisional application at the United States Patent and Trademark Office (5/20 - 8/20/03: G. Bardmesser);
GS Bardmesser	05/21/2003	1875	4170000	High Voltage Power M	2.30	work on application, specification, claims and figures;
GS Bardmesser	06/02/2003	1875	4170000	High Voltage Power M	1.30	work on application, specification claims and figures;
GS Bardmesser	07/01/2003	1875	4170000	High Voltage Power M	1.90	Maintenance Change.
GS Bardmesser	08/07/2003	1875	4170000	High Voltage Power M	0.80	telephone conference with inventor; revise application per inventor comments;
GS Bardmesser	08/08/2003	1875	4170000	High Voltage Power M	0.50	revise application per inventor comments; prepare formal documents;
GS Bardmesser	08/19/2003	1875	4170000	High Voltage Power M	0.20	prepare documents for filing application;
GS Bardmesser	08/20/2003	1875	4170000	High Voltage Power M	0.50	file non-provisional at the United States Patent and Trademark Office;
JT Helvey	07/03/2003	1875	4170000	High Voltage Power M	2.50	2nd eye application;
JT Helvey	07/10/2003	1875	4170000	High Voltage Power M	0.60	
JT Helvey	08/11/2003	1875	4170000	High Voltage Power M	0.40	attention to final draft, filing documents, and send same to the inventor;
JT Helvey	08/20/2003	1875	4170000	High Voltage Power M	0.30	2nd eye application filing;

Timekeeper Na	Date	Client	Matter	Matter Desc	Hours	Description
GS Bardmesser	04/23/2003	1875	4150000	Power Management Uni	5.50	work on application, specification, claims and figures (BP 2866, 2865 and 2864)
GS Bardmesser	04/29/2003	1875	4150000	Power Management Uni	2.80	work on application, specification, claims and figures;
GS Bardmesser	04/30/2003	1875	4150000	Power Management Uni	2.10	work on application, specification, claims and figures;
GS Bardmesser	05/01/2003	1875	4150000	Power Management Uni	1.80	work on application, specification, claims and figures;
GS Bardmesser	05/05/2003	1875	4150000	Power Management Uni	1.90	work on application, claims and figures;
GS Bardmesser	05/08/2003	1875	4150000	Power Management Uni	2.00	work on application, specification, claims and figures;
GS Bardmesser	05/09/2003	1875	4150000	Power Management Uni	1.90	work on application, specification, claims and figures;
GS Bardmesser	05/12/2003	1875	4150000	Power Management Uni	1.10	finalize and file application at the United States Patent and Trademark Office (5/12 - 8/20/03: G. Bardmesser);
GS Bardmesser	05/13/2003	1875	4150000	Power Management Uni	2.20	work on application, specification, claims and figures;
GS Bardmesser	05/14/2003	1875	4150000	Power Management Uni	1.40	work on application, specification, claims and figures;
GS Bardmesser	05/15/2003	1875	4150000	Power Management Uni	1.60	work on application, specification, claims and figures;
GS Bardmesser	05/16/2003	1875	4150000	Power Management Uni	2.20	work on application, specification, claims and figures;
GS Bardmesser	05/19/2003	1875	4150000	Power Management Uni	0.70	work on application, specification, claims and figures;
GS Bardmesser	05/20/2003	1875	4150000	Power Management Uni	1.70	work on application, specification, claims and figures;
GS Bardmesser	05/21/2003	1875	4150000	Power Management Uni	2.20	work on applicaiton, specification, claims and figures;
GS Bardmesser	06/02/2003	1875	4150000	Power Management Uni	1.20	work on application, specification claims and figures;
GS Bardmesser	08/07/2003	1875	4150000	Power Management Uni	0.80	telephone conference with inventor; revise application per inventor comments;
GS Bardmesser	08/08/2003	1875	4150000	Power Management Uni	0.50	revise application per inventor comments; prepare formal documents;
GS Bardmesser	08/19/2003	1875	4150000	Power Management Uni	0.20	prepare documents for filing application;
GS Bardmesser	08/20/2003	1875	4150000	Power Management Uni	0.60	file non-provisional at the United States Patent and Trademark Office;

JT Helvey	03/18/2003	1875	4150000	Power Management Uni	(3.00)		Maintenance Change.
JT Helvey	03/18/2003	1875	4150000	Power Management Uni	3.00		prepare and forward application to inventor for review (3/18 - 7/10/03: J. Helvey & G. Bardmesser);
JT Helvey	03/19/2003	1875	4150000	Power Management Uni	(1.50)		Maintenance Change.
JT Helvey	03/19/2003	1875	4150000	Power Management Uni	1.50		travel from Los Angeles to D.C.. (Move to BP 2869, BP 2866 and BP 2865 when open.)
JT Helvey	05/01/2003	1875	4150000	Power Management Uni	3.00		Maintenance Change.
JT Helvey	05/01/2003	1875	4150000	Power Management Uni	1.50		Maintenance Change.
JT Helvey	07/02/2003	1875	4150000	Power Management Uni	2.00		2nd eye first draft of application;
JT Helvey	07/10/2003	1875	4150000	Power Management Uni	0.60		revise application, and send same to the inventor;
JT Helvey	08/11/2003	1875	4150000	Power Management Uni	0.40		attention to final draft, filing documents, and send same to the inventor;
JT Helvey	08/20/2003	1875	4150000	Power Management Uni	0.30		2nd eye application filing;
RE Sokohl	03/18/2003	1875	4150000	Power Management Uni	(1.00)		Maintenance Change.
RE Sokohl	03/18/2003	1875	4150000	Power Management Uni	(1.00)		Maintenance Change.
RE Sokohl	03/18/2003	1875	4150000	Power Management Uni	(1.00)		Maintenance Change.
RE Sokohl	03/18/2003	1875	4150000	Power Management Uni	1.00		internal office conference with C.Y. Chen;
RE Sokohl	03/18/2003	1875	4150000	Power Management Uni	1.00		internal office conference with C. Y. Chen;
RE Sokohl	03/18/2003	1875	4150000	Power Management Uni	1.00		internal office conference with C.Y. Chen and J. Helvey regarding BP 2864, 65 and 66;
RE Sokohl	04/30/2003	1875	4150000	Power Management Uni	0.20		attention to matter;
RE Sokohl	05/01/2003	1875	4150000	Power Management Uni	1.00		Maintenance Change.
RE Sokohl	05/01/2003	1875	4150000	Power Management Uni	1.00		Maintenance Change.
RE Sokohl	05/01/2003	1875	4150000	Power Management Uni	1.00		Maintenance Change.

Timekeeper N	Date	Clien	Matter I	Matter Desc	Hours	Description
GS Bardmesser	04/24/2003	1875	4160000	Low Leakage CMOS Pow	6.50	prepare and forward application to inventor for review (4/24 - 7/10/03: G. Bardmesser & J. Helvey);
GS Bardmesser	04/29/2003	1875	4160000	Low Leakage CMOS Pow	2.60	work on application, specification, claims and figures;
GS Bardmesser	04/30/2003	1875	4160000	Low Leakage CMOS Pow	2.00	work on application, specification, claims and figures;
GS Bardmesser	05/01/2003	1875	4160000	Low Leakage CMOS Pow	1.80	work on application, specification, claims and figures;
GS Bardmesser	05/05/2003	1875	4160000	Low Leakage CMOS Pow	1.90	work on application, specification, claims and figures;
GS Bardmesser	05/08/2003	1875	4160000	Low Leakage CMOS Pow	2.00	work on application, specification, claims and figures;
GS Bardmesser	05/09/2003	1875	4160000	Low Leakage CMOS Pow	1.90	work on application, specification, claims and figures;
GS Bardmesser	05/13/2003	1875	4160000	Low Leakage CMOS Pow	2.20	work on application, specification, claims and figures;
GS Bardmesser	05/14/2003	1875	4160000	Low Leakage CMOS Pow	1.40	work on application, specification, claims and figures;
GS Bardmesser	05/15/2003	1875	4160000	Low Leakage CMOS Pow	1.50	work on application, specification, claims and figures;
GS Bardmesser	05/16/2003	1875	4160000	Low Leakage CMOS Pow	2.20	work on application, specification, claims and figures;
GS Bardmesser	05/19/2003	1875	4160000	Low Leakage CMOS Pow	0.70	work on application, specification, claims and figures;
GS Bardmesser	05/20/2003	1875	4160000	Low Leakage CMOS Pow	1.70	finalize and file non-provisional application at the United States Patent and Trademark Office (5/20 - 8/20/03: G. Bardmesser);
GS Bardmesser	05/21/2003	1875	4160000	Low Leakage CMOS Pow	2.20	work on application, specification, claims and figures;
GS Bardmesser	06/02/2003	1875	4160000	Low Leakage CMOS Pow	1.20	work on application, specification claims and figures;
GS Bardmesser	08/07/2003	1875	4160000	Low Leakage CMOS Pow	0.80	telephone conference with inventor; revise application per inventor comments;
GS Bardmesser	08/08/2003	1875	4160000	Low Leakage CMOS Pow	0.50	revise application per inventor comments; prepare formal documents;
GS Bardmesser	08/11/2003	1875	4160000	Low Leakage CMOS Pow	0.30	revise specification;
GS Bardmesser	08/19/2003	1875	4160000	Low Leakage CMOS Pow	0.20	prepare documents for filing application;
GS Bardmesser	08/20/2003	1875	4160000	Low Leakage CMOS Pow	0.50	file non-provisional at the United States Patent and Trademark Office;
JT Helvey	07/03/2003	1875	4160000	Low Leakage CMOS Pow	2.50	2nd eye application;
JT Helvey	07/10/2003	1875	4160000	Low Leakage CMOS Pow	0.60	
JT Helvey	08/11/2003	1875	4160000	Low Leakage CMOS Pow	0.40	attention to final draft, filing documents, and send same to the inventor;
JT Helvey	08/20/2003	1875	4160000	Low Leakage CMOS Pow	0.30	2nd eye application filing;

Sterne Kessler Goldstein Fox
ATTORNEYS AT LAW

August 11, 2003

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INTERNET ADDRESS:
JHELVEY@SKGF.COM

Mr. Chun-Ying Chen
Broadcom Corporation
16215 Alton Parkway
Irvine, CA 92618-3616

Via Federal Express

Re: Final Draft of U.S. Patent Application
For: **High Voltage Power Management Unit Architecture In CMOS Process**
Inventors: Chen *et al.*
Your Ref: BP 2866
Our Ref: 1875.4170000/JTH/GSB

Dear CY:

Enclosed please find the final draft of the U.S. patent application for the above-referenced matter. The application has been revised in accordance with your comments. Thus, the application should now be in a condition for filing with the U.S. Patent and Trademark Office (USPTO).

We request that you and Hsiang-bin Lee review the enclosed application. We make no representations or warrants as to the patentability of the invention as claimed. Prior to drafting this application, a search of the prior art **was not** performed. Even if a search of the prior art was performed, we may not have uncovered all prior art of interest to an examiner. The art that was reviewed in preparing the Background of the Invention may not be the closest prior art. There may be art, of which we are unaware, and have not discussed, that may detract from the patentability of this invention.

If the application meets with your approval, then we request that the following documents be executed and returned to us for filing with the application:

1. ***A Declaration***. Please carefully review the Declaration and any information that we have entered onto it and fill in any missing

information in blue ink. By "residence" address is meant the city and state of residence, or, if residence is not in the United States, city and country of residence. The "mailing" address is the (full) address at which the inventor customarily receives mail; either the home or business address is acceptable as a mailing address. After you and the other inventor have completed the review of the patent application, any amendments, and Declaration, and if the information in the Declaration is correct and complete, you should **sign and date** the Declaration in blue ink where indicated. If any corrections are made, please initial and date the corrections in the margin.

2. ***An Assignment***. Please review the Assignment document. In the body of the Assignment, in the blank space after the words "... **executed by the undersigned on ____**," you and the other inventor should enter the date that they signed the ***Declaration***. Then, you should sign and date the bottom of the Assignment document in blue ink.

Every person who signs a document that is submitted to the USPTO makes a certification under 37 C.F.R. § 10.18(b). A copy of 37 C.F.R. § 10.18(b) and (c) is attached. Every individual who signs one of the enclosed documents should review this rule.

Please return the enclosed application (including the drawings) and the executed formal documents to us so that we may file them with the USPTO. Please use an overnight courier, such as Federal Express, to send these papers to us. We request that you attend to this matter at your earliest convenience.

A duty of disclosure continues throughout the entire patent application process, and ends only with the actual issuance of a patent. Therefore, if anyone substantively involved in the patent application process becomes aware of information that might be considered material, please forward it to us immediately. If there is information to submit, USPTO rules provide certain advantages to the applicant if the information is submitted within three months of the filing of the application, or before the examiner issues an office action on the merits, whichever is later.

Please note that most countries require absolute novelty of the invention. Therefore, if you have any interest in filing this subject matter outside of the United States, please let us know as soon as possible, preferably prior to any disclosure or submission (written, oral, or electronic) of the subject matter to a third party.

Also, unless we request otherwise when the application is filed, this application will be published approximately 18 months from its earliest U.S. filing date. If the invention has not

been and will not be the subject of an application filed in another country (or under international agreement) that requires eighteen-month publication, then the applicant can request that the application not be published.

While the non-publication request may be rescinded at any time, you should not file a non-publication request if you intend to internationally file this application. If the application is subsequently filed in another country (or under international agreement) that requires eighteen-month publication, we must notify the USPTO within forty-five (45) days or the application will become abandoned. Because the vast majority of applications are filed both in the United States and outside of the United States, we will **not** file a non-publication request unless we have your express instructions to do so.

Please contact us if you have any questions or comments regarding the foregoing.

Very truly yours,

STERNE, KESSLER, GOLDSTEIN & FOX P.L.L.C.

Jeffrey T. Helvey

JTH/GSB:krh

Enclosures

cc: Hsiang-bin Lee (w/encl.)

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